

## High power PNP epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = -140 V
- Complementary to 2STC4468
- Typical f<sub>t</sub> = 20 MHz
- Fully characterized at 125 °C

### **Applications**

■ Audio power amplifier

#### **Description**

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stage.

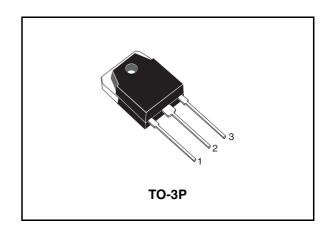


Figure 1. Internal schematic diagram

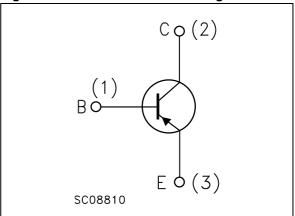


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA1695	2STA1695	TO-3P	Tube

Electrical ratings 2STA1695

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	-140	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	-140	V
$V_{EBO}$	Emitter-base voltage (I <sub>C</sub> = 0)	-6	V
I <sub>C</sub>	Collector current	-10	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	-20	А
P <sub>tot</sub> Total dissipation at T <sub>c</sub> = 25 °C		100	W
T <sub>stg</sub> Storage temperature		-65 to 150	°C
TJ	T <sub>J</sub> Max. operating junction temperature		°C

Table 3. Thermal data

	Symbol	Parameter		Value	Unit
Ī	R <sub>thj-case</sub>	Thermal resistance junction-case	max	1.25	°C/W

# 2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = -140 V			-0.1	μА
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = -6 V			-0.1	μΑ
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = -50 mA	-140			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -100 μA	-140			V
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = -1 mA	-6			V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = -5 \text{ A}$ $I_B = -500 \text{ mA}$ $I_C = -7 \text{ A}$ $I_B = -700 \text{ mA}$			-0.5 -0.7	V V
V <sub>BE</sub> <sup>(1)</sup>	Base-emitter voltage	$V_{CE} = -5 \text{ V}$ $I_{C} = -5 \text{ A}$			-1.3	V
h <sub>FE</sub>	DC current gain	$I_{C} = -3 \text{ A}$ $V_{CE} = -4 \text{ V}$ $I_{C} = -5 \text{ A}$ $V_{CE} = -4 \text{ V}$	70 50		140	
f <sub>T</sub>	Transition frequency	$I_C = -0.5 \text{ A}$ $V_{CE} = -12 \text{ V}$		20		MHz
C <sub>CBO</sub>	Collector-base capacitance $(I_E = 0)$	V <sub>CB</sub> = -10 V		225		pF
	Resistive load					
t <sub>on</sub>	Turn-on time	$I_C = -5 \text{ A}$ $V_{CC} = -60 \text{ V}$		0.24		μs
t <sub>stg</sub>	Storage time	$I_{B1} = -I_{B2} = -0.5 \text{ A}$		1.2		μs
t <sub>f</sub>	Fall time			0.24		μs

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu s$ , duty cycle  $\leq$  1.5 %

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Electrical characteristics 2STA1695

### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Output characteristics

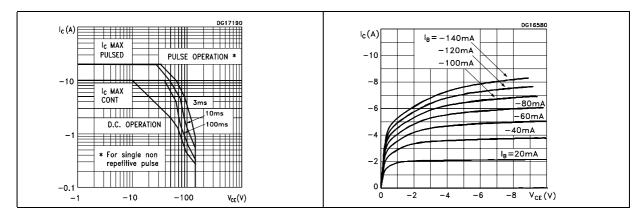


Figure 4. DC current gain

Figure 5. Collector-emitter saturation voltage

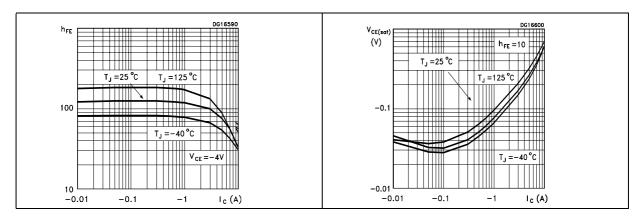
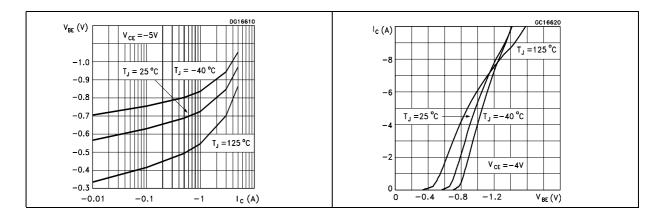


Figure 6. Base-emitter voltage

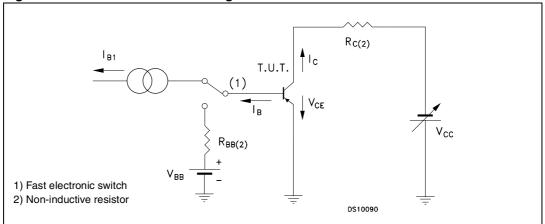
Figure 7. Base-emitter voltage



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## 2.2 Test circuit

Figure 8. Resistive load switching test circuit

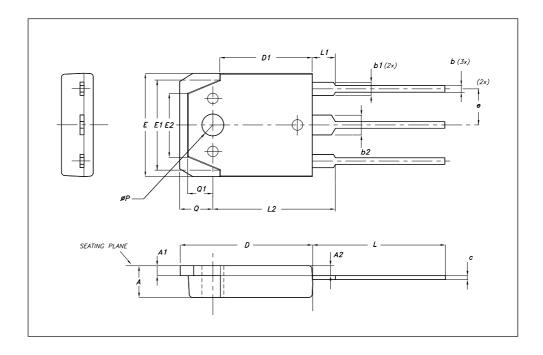


# 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

#### **TO-3P Mechanical data**

DIM.		mm.	
	MIN.	TYP	MAX.
Α	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
С	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
е	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
Р	3.10		3.30
Q		5	
Q1		3.80	



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Revision history 2STA1695

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes	
18-May-2007	1	Initial release	
06-Nov-2008	2	Document status promoted from preliminary data to datasheet.	

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